

IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (Currently Amended): A method of correcting manufacturing a photomask comprising the steps of:

(a) calculating making a first correction for correcting a configuration of a mask pattern of said photomask in accordance with:

a space between said mask pattern and an adjacent mask pattern thereto, and a desired configuration to be transferred from said mask pattern;

(b) dividing said photomask into a plurality of regions; and

(b) (c) calculating making a second correction for dividing said photomask into a plurality of regions, thereby correcting a of said configuration of [[a]] said mask pattern of said photomask in accordance with an occupation rate of said mask pattern in each of said plurality of regions, said first correction having an effect in a smaller range than said second correction; and

(d) correcting said photomask based on said first correction and said second correction.

Claim 2 (Canceled).

Claim 3 (Original): The method according to claim 1, wherein said first and second corrections are made independently.

Claim 4 (Original): The method according to claim 1, wherein said second correction is made based on a correction table generated in accordance with said occupation rate of said mask pattern.

Claim 5 (Original): The method according to claim 1, wherein  
said second correction is made based on a correction function using said occupation  
rate of said mask pattern as a variable.

Claim 6 (Currently Amended): The method according to claim 1, wherein  
in said second correction, a size by which said photomask is divided into said  
plurality of regions is selected for each ~~changed by~~ a correction factor.

Claim 7 (Original): The method according to claim 6, wherein  
said correction factor includes a plurality of correction factors, and  
said second correction performs a correction for each of said plurality of correction  
factors.

Claims 8 and 9 (Canceled).

Claim 10 (New): A method of correcting a photomask comprising:  
(a) calculating a first correction for correcting a configuration of a mask pattern of  
said photomask in accordance with:  
a space between said mask pattern and an adjacent mask pattern thereto, and  
a desired configuration to be transferred from said mask pattern;  
(b) dividing said photomask into a plurality of regions;  
(c) calculating a second correction of said configuration of said mask pattern of said  
photomask in accordance with an occupation rate of said mask pattern in each of said  
plurality of regions, wherein said occupation rate in an arbitrary region is the average of

occupation rates of said mask pattern in regions adjacent to said arbitrary region, said first correction having an effect in a smaller range than said second correction; and

(d) correcting said photomask based on said first correction and said second correction.

Claim 11 (New): The method according to claim 10, wherein said first and second corrections are made independently.

Claim 12 (New): The method according to claim 10, wherein said second correction is made based on a correction table generated in accordance with said occupation rate of said mask pattern.

Claim 13 (New): The method according to claim 10, wherein said second correction is made based on a correction function using said occupation rate of said mask pattern as a variable.

Claim 14 (New): The method according to claim 10, wherein in said second correction, a size by which said photomask is divided into said plurality of regions is selected for each correction factor.

Claim 15 (New): The method according to claim 14, wherein said correction factor includes a plurality of correction factors, and said second correction performs a correction for each of said plurality of correction factors.

Claim 16 (New): A method of correcting a photomask comprising:

(a) calculating a first correction for correcting a configuration of a mask pattern of said photomask in accordance with:

a space between said mask pattern and an adjacent mask pattern thereto, and

a desired configuration to be transferred from said mask pattern;

(b) dividing said photomask into a plurality of regions; and

(c) calculating a second correction of said configuration of said mask pattern of said photomask in accordance with an occupation rate of said mask pattern in each of said plurality of regions, wherein when an arbitrary mask pattern occupies more than one region of said plurality of regions, said second correction of each region occupied by said arbitrary mask pattern is the average of second corrections of all regions occupied by said arbitrary mask pattern, said first correction having an effect in a smaller range than said second correction; and

(d) correcting said photomask based on said first correction and said second correction.

Claim 17 (New): The method according to claim 16, wherein

said first and second corrections are made independently.

Claim 18 (New): The method according to claim 16, wherein

said second correction is made based on a correction table generated in accordance with said occupation rate of said mask pattern.

Claim 19 (New): The method according to claim 16, wherein  
said second correction is made based on a correction function using said occupation  
rate of said mask pattern as a variable.

Claim 20 (New): The method according to claim 16, wherein  
in said second correction, a size by which said photomask is divided into said  
plurality of regions is selected for each correction factor.

Claim 21 (New): The method according to claim 20, wherein  
said correction factor includes a plurality of correction factors, and  
said second correction performs a correction for each of said plurality of correction  
factors.